



FDFM2N111 Information



For Reference Only

Part Number FDFM2N111

 Manufacturer
 Fairchild/ON Semiconductor

 Category
 Discrete Semiconductor Products

 Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 20V 4A 3X3 MLP

Package 6-MLP, Power33

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









FDFM2N111 Specifications

Manufacturer Part NumberFDFM2N111ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackage6-MLP, Power33SeriesPowerTrench?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs3.8nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds273pF @ 10VVgs (Max)±12VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.7W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 4A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 6-MLP, Power33 Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 1.5V @ 250µA 3.8nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 273pF @ 10V Vgs (Max) FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.7W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case	Manufacturer Part Number	FDFM2N111
Package 6-MLP, Power33 Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 3.8nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 273pF @ 10V Vgs (Max) ±12V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 1.7W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Manufacturer	Fairchild/ON Semiconductor
Package 6-MLP, Power33 Series PowerTrench? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 3.8nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 273pF @ 10V Vgs (Max) ±12V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 1.7W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Category	Discrete Semiconductor Products
SeriesPowerTrench?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs3.8nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds273pF @ 10VVgs (Max)±12VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.7W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 4A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 20V Current - Continuous Drain (Id) @ 25°C 4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 3.8nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 273pF @ 10V Vgs (Max) ±12V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 1.7W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Package	6-MLP, Power33
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs3.8nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds273pF @ 10VVgs (Max)±12VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.7W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 4A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33	Series	PowerTrench?
Drain to Source Voltage (Vdss)20VCurrent - Continuous Drain (Id) @ 25°C4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs3.8nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds273pF @ 10VVgs (Max)±12VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.7W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 4A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 3.8nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±12V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.7W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.5V @ 250μAGate Charge (Qg) (Max) @ Vgs3.8nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds273pF @ 10VVgs (Max)±12VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.7W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 4A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33	Drain to Source Voltage (Vdss)	20V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 1.5V @ 250μA 3.8nC @ 4.5V 273pF @ 10V 273pF @ 10	Current - Continuous Drain (Id) @ 25°C	4A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 273pF @ 10V Vgs (Max) ±12V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Drive Voltage (Max Rds On, Min Rds On)	2.5V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Vgs(th) (Max) @ Id	1.5V @ 250μA
Vgs (Max)±12VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.7W (Ta)Rds On (Max) @ Id, Vgs100 mOhm @ 4A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33	Gate Charge (Qg) (Max) @ Vgs	3.8nC @ 4.5V
FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 1.7W (Ta) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Input Capacitance (Ciss) (Max) @ Vds	273pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 100 mOhm @ 4A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Vgs (Max)	±12V
Rds On (Max) @ Id, Vgs100 mOhm @ 4A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33	FET Feature	Schottky Diode (Isolated)
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Power Dissipation (Max)	1.7W (Ta)
Mounting TypeSurface MountSupplier Device PackageMicroFET 3x3mmPackage / Case6-MLP, Power33	Rds On (Max) @ Id, Vgs	100 mOhm @ 4A, 4.5V
Supplier Device Package MicroFET 3x3mm Package / Case 6-MLP, Power33	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 6-MLP, Power33	Mounting Type	Surface Mount
	Supplier Device Package	MicroFET 3x3mm
Report errors?	Package / Case	6-MLP, Power33
		Report errors?

FDFM2N111 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FDFM2N111 Payment Methods

































If you have any question about FDFM2N111, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com